

# NTPF150N65S3HF

## MOSFET – Power, N-Channel, SUPERFET III, FRFET

**650 V, 24 A, 150 mΩ**

### Description

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III MOSFET is very suitable for the various power system for miniaturization and higher efficiency.

SUPERFET III FRFET MOSFET's optimized reverse recovery performance of body diode can remove additional component and improve system reliability.

### Features

- 700 V @  $T_J = 150^\circ\text{C}$
- Typ.  $R_{DS(on)} = 121\text{ m}\Omega$
- Ultra Low Gate Charge (Typ.  $Q_g = 43\text{ nC}$ )
- Low Effective Output Capacitance (Typ.  $C_{oss(eff.)} = 400\text{ pF}$ )
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

### Applications

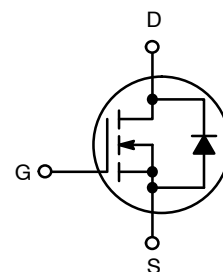
- Telecom / Server Power Supplies
- Industrial Power Supplies
- EV Charger
- UPS / Solar



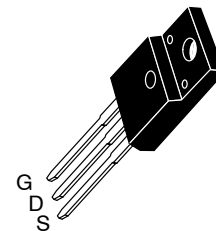
ON Semiconductor®

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$V_{DSS}$	$R_{DS(on)}\text{ MAX}$	$I_D\text{ MAX}$
650 V	150 mΩ @ 10 V	24 A

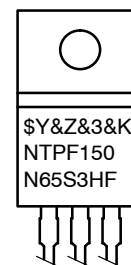


POWER MOSFET



TO-220 FULLPAK  
CASE 221D

### MARKING DIAGRAM



\$Y = ON Semiconductor Logo  
&Z = Assembly Plant Code  
&3 = Numeric Date Code  
&K = Lot Code  
NTPF150N65S3HF = Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# NTPF150N65S3HF

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C, Unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>DSS</sub>	Drain to Source Voltage	650	V
V <sub>GSS</sub>	Gate to Source Voltage	- DC	±30
		- AC (f > 1 Hz)	±30
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°C)	24*
		- Continuous (T <sub>C</sub> = 100°C)	15.2*
I <sub>DM</sub>	Drain Current	- Pulsed (Note 1)	60*
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	275	mJ
I <sub>AS</sub>	Avalanche Current (Note 2)	3.8	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	1.92	mJ
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt (Note 3)	50	
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C)	192
		- Derate Above 25°C	1.54
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

\*Drain current limited by maximum junction temperature.

1. Repetitive rating; pulse-width limited by maximum junction temperature.
2. I<sub>AS</sub> = 3.8 A, R<sub>G</sub> = 25 Ω, starting T<sub>J</sub> = 25°C.
3. I<sub>SD</sub> ≤ 12 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ 400 V, starting T<sub>J</sub> = 25°C.

## THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction to Case, Max.	3.22	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient, Max.	62.5	

## PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
NTPF150N65S3HF	NTPF150N65S3HF	TO-220 FULLPACK	Tube	N/A	N/A	50 Units

# NTPF150N65S3HF

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	650			V
		$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 150^\circ\text{C}$	700			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 15\text{ mA}$ , Referenced to $25^\circ\text{C}$		0.62		V/ $^\circ\text{C}$
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$			10	$\mu\text{A}$
		$V_{DS} = 520\text{ V}, T_C = 125^\circ\text{C}$		67		
I <sub>GSS</sub>	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$			$\pm 100$	nA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 0.54\text{ mA}$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 12\text{ A}$		121	150	m $\Omega$
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = 20\text{ V}, I_D = 12\text{ A}$		14		S

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1985		pF
C <sub>oss</sub>	Output Capacitance			40		pF
C <sub>oss(eff.)</sub>	Effective Output Capacitance	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$		400		pF
C <sub>oss(er.)</sub>	Energy Related Output Capacitance	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$		71		pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10 V	$V_{DS} = 400\text{ V}, I_D = 12\text{ A}, V_{GS} = 10\text{ V}$ (Note 4)		43		nC
Q <sub>gs</sub>	Gate to Source Gate Charge			13		nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge			17		nC
ESR	Equivalent Series Resistance	$f = 1\text{ MHz}$		5.0		$\Omega$

### SWITCHING CHARACTERISTICS

t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 400\text{ V}, I_D = 12\text{ A}, V_{GS} = 10\text{ V}$ $R_g = 4.7\text{ }\Omega$ (Note 4)		21		ns
t <sub>r</sub>	Turn-On Rise Time			19		ns
t <sub>d(off)</sub>	Turn-Off Delay Time			63		ns
t <sub>f</sub>	Turn-Off Fall Time			14		ns

### SOURCE-DRAIN DIODE CHARACTERISTICS

I <sub>S</sub>	Maximum Continuous Source to Drain Diode Forward Current			24		A
I <sub>SM</sub>	Maximum Pulsed Source to Drain Diode Forward Current			60		A
V <sub>SD</sub>	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_{SD} = 12\text{ A}$		1.3		V
t <sub>rr</sub>	Reverse Recovery Time	$V_{DD} = 400\text{ V}, I_{SD} = 12\text{ A},$ $di_F/dt = 100\text{ A}/\mu\text{s}$		88		ns
Q <sub>rr</sub>	Reverse Recovery Charge			306		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

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## TYPICAL CHARACTERISTICS

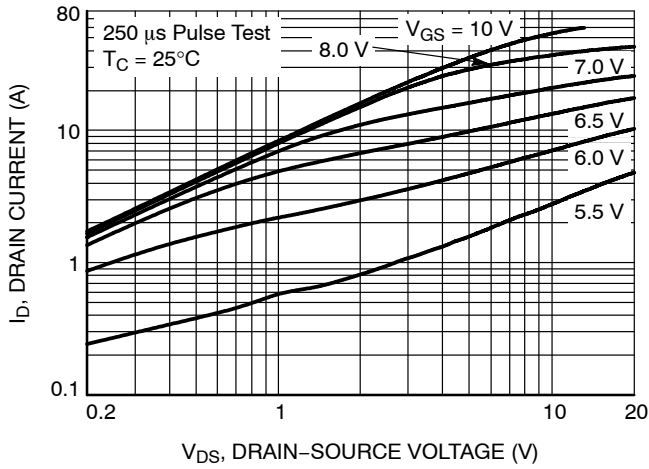


Figure 1. On-Region Characteristics

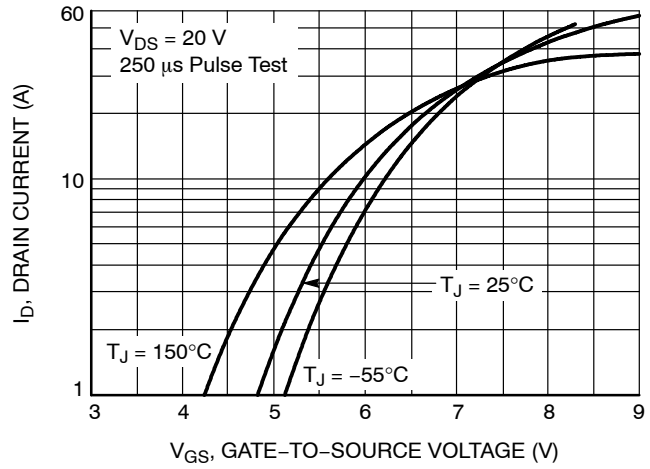


Figure 2. Transfer Characteristics

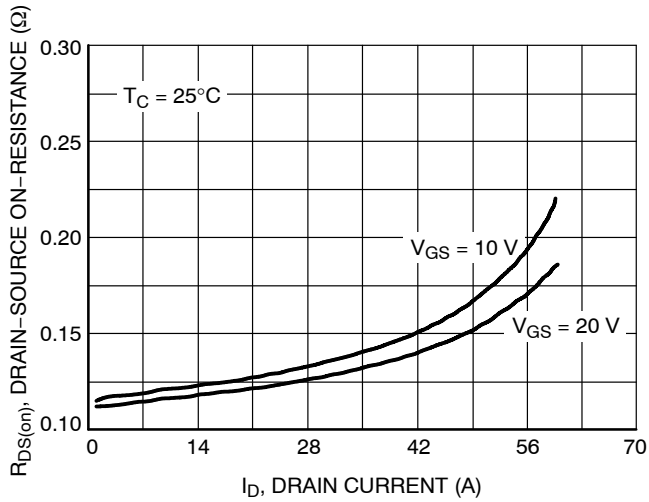


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

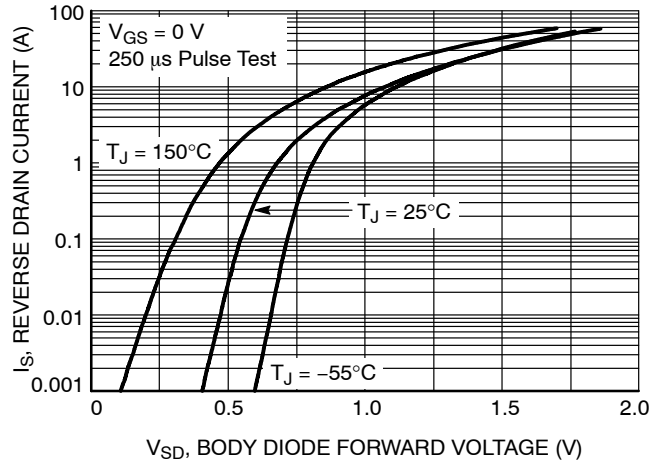


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

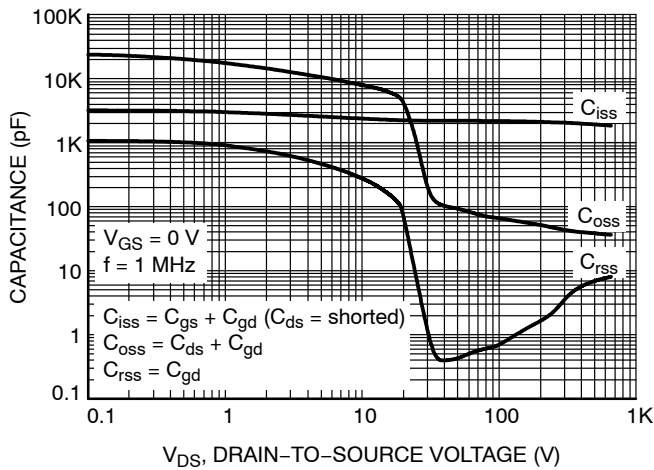


Figure 5. Capacitance Characteristics

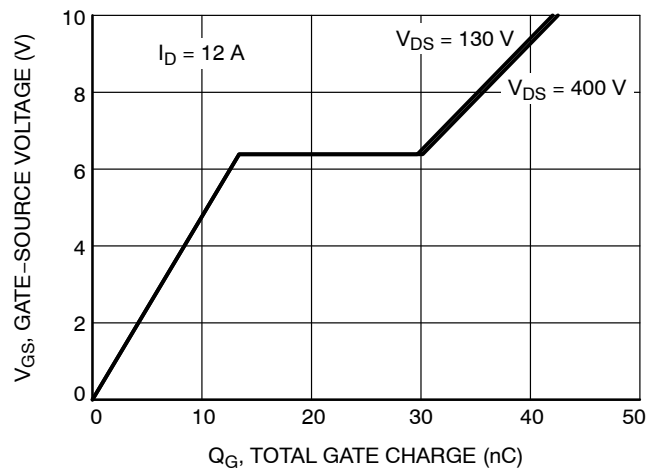
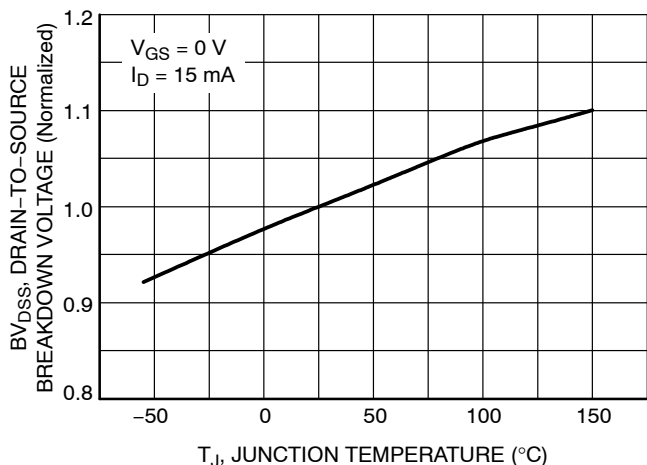


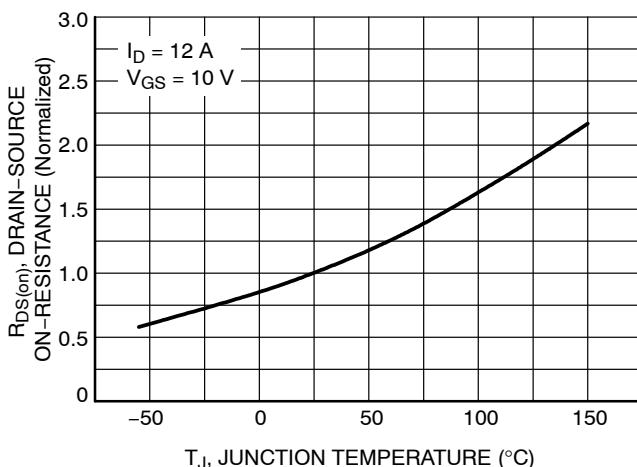
Figure 6. Gate Charge Characteristics

# NTPF150N65S3HF

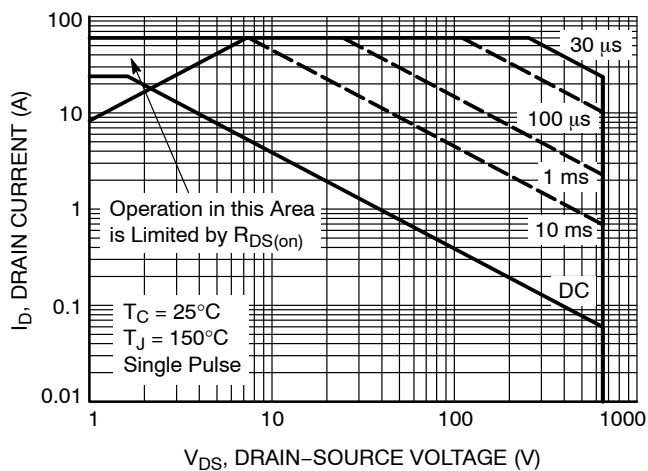
## TYPICAL CHARACTERISTICS



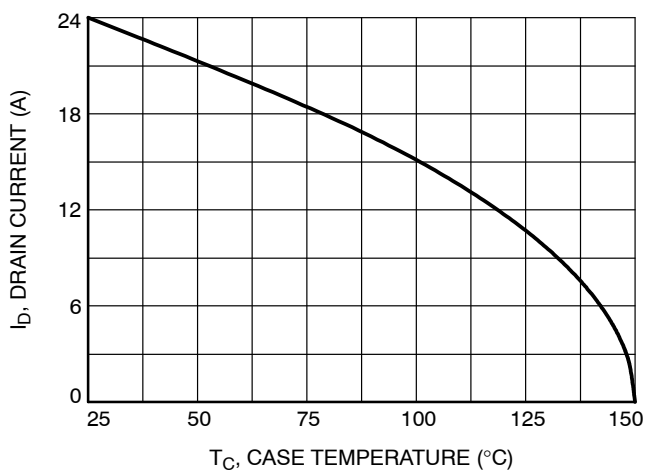
**Figure 7. Breakdown Voltage Variation vs. Temperature**



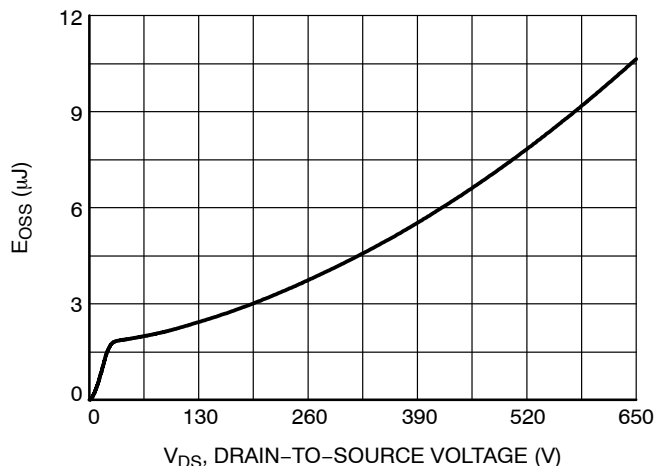
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**



**Figure 11.  $E_{OSS}$  vs. Drain-to-Source Voltage**

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## TYPICAL CHARACTERISTICS

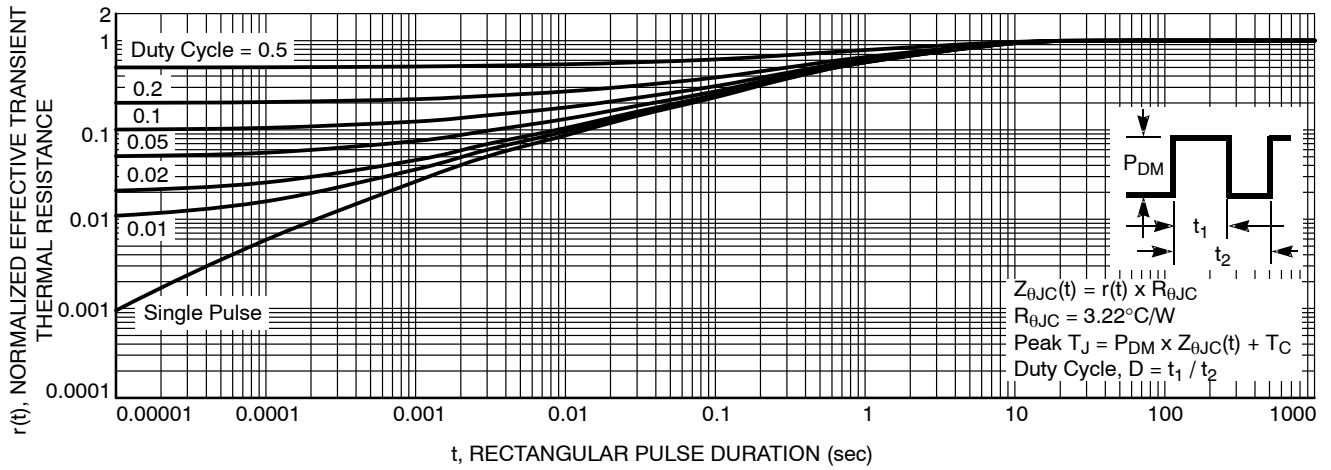


Figure 12. Transient Thermal Response Curve

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Figure 13. Gate Charge Test Circuit & Waveform

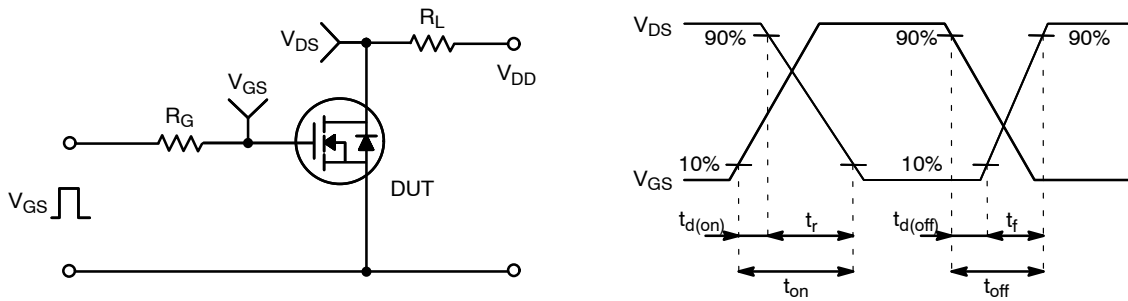


Figure 14. Resistive Switching Test Circuit & Waveforms

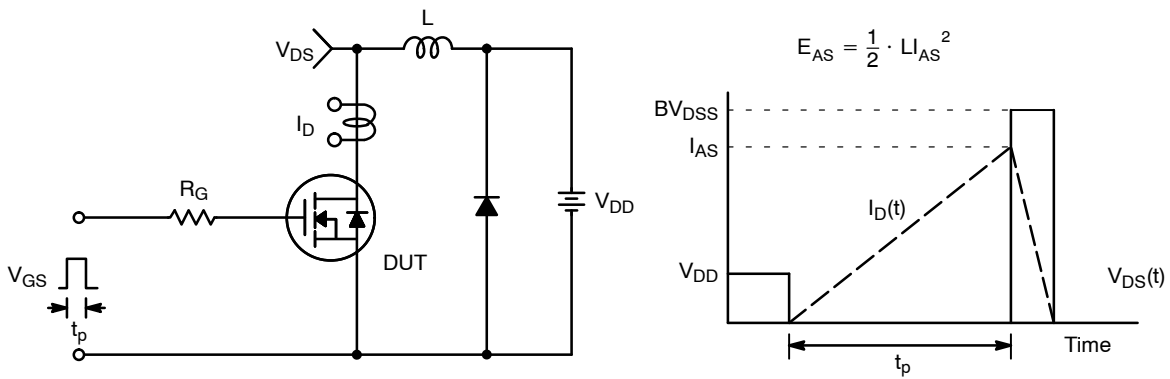


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

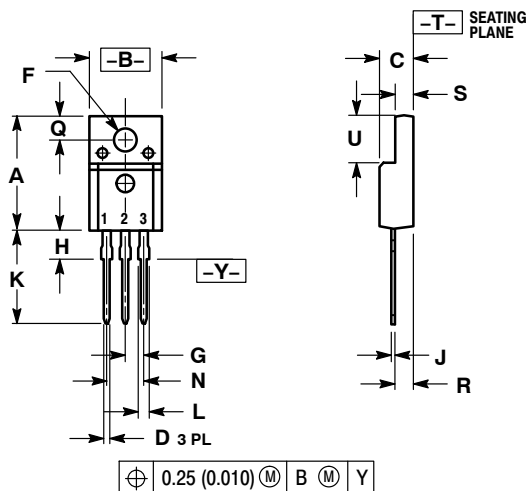




# NTPF150N65S3HF

## PACKAGE DIMENSIONS

### TO-220 FULLPAK CASE 221D-03 ISSUE K



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH
  3. 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.617	0.635	15.67	16.12
B	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
H	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

⊕ 0.25 (0.010) M B M Y

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